

# Vacuum Electron Device Limitations for High-Power RF Sources

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# Vacuum Electron Device Limitations for High-Power RF Sources

Devices discussed in this presentation:

## CW and High Average Power Amplifiers

- Single-Beam Klystrons
- Multi-Beam Klystrons (MBK)
- Single-Beam Inductive Output Tubes (IOT)
- Higher-Order-Mode IOT (HOM-IOT)

## Vacuum Electron Device Limitations for High-Power RF Sources

CW and High Average Power Devices not (yet) considered here:

- Sheet Beam Klystrons (early state of development)
- Coaxial IOT (early state of development)
- Gyrotrons
- Traveling Wave Tubes

## Vacuum Electron Device Limitations for High-Power RF Sources

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### Warning:

- Numerous papers on this subject have been written already.
- Device limitations are shifting with time and effort.
- “Absolute” limits have been proven wrong, again and again.

### Thus:

- In the limited time frame available, just expect a chat about some of the borderlines that are presently under siege.

# Vacuum Electron Device Limitations for High-Power RF Sources

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## Limitations discussed in the following

### VED technology related

- Size
- Output window capability
- Output cavity capability
- HV breakdown in electron guns
- Cathode emission limitations

### Other reasons

- Manufacturing capacity
- Reproducibility
- Demand
- “Blinkers”

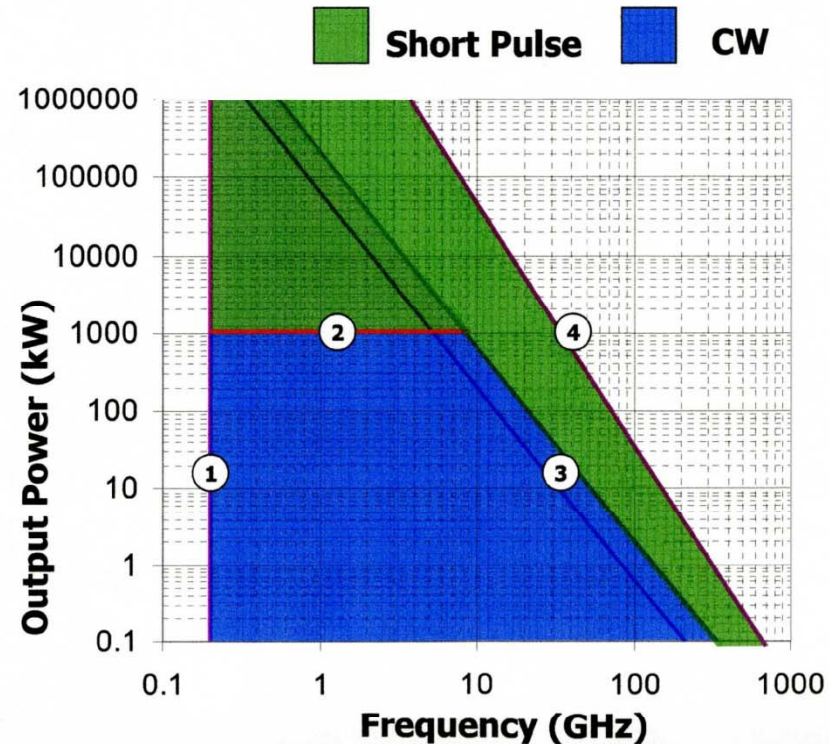
# Vacuum Electron Device Limitations for High-Power RF Sources

## Klystron technology limitations (debated)

- Plot showing the PF spectrum for klystrons, both short pulse and CW

- Approximate limitations

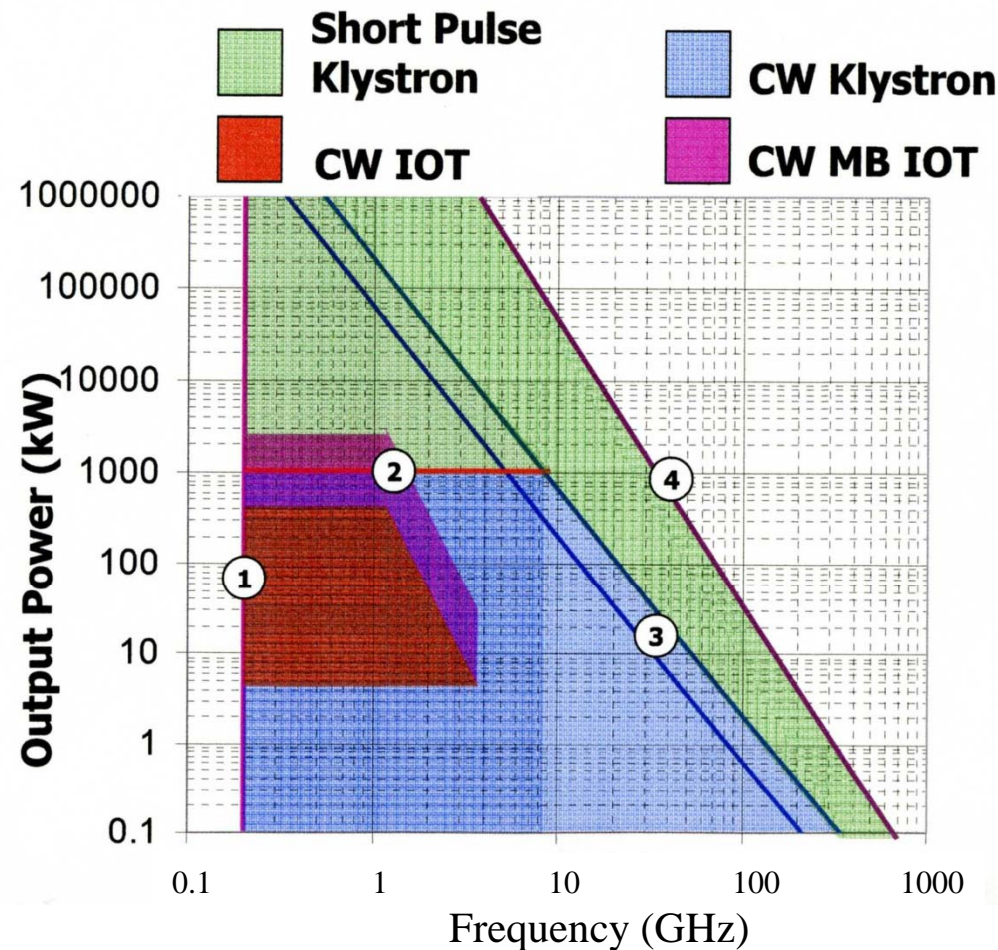
- (1) Size (CW & Pulsed)
- (2) Window (CW)
- (3) O/P Cavity Power Density / Cyclical Fatigue (CW)
- (4) RF Breakdown (Pulsed)





# Vacuum Electron Device Limitations for High-Power RF Sources

Considerable part of former klystron domain claimed by IOTs



Why?

# Vacuum Electron Device Limitations for High-Power RF Sources

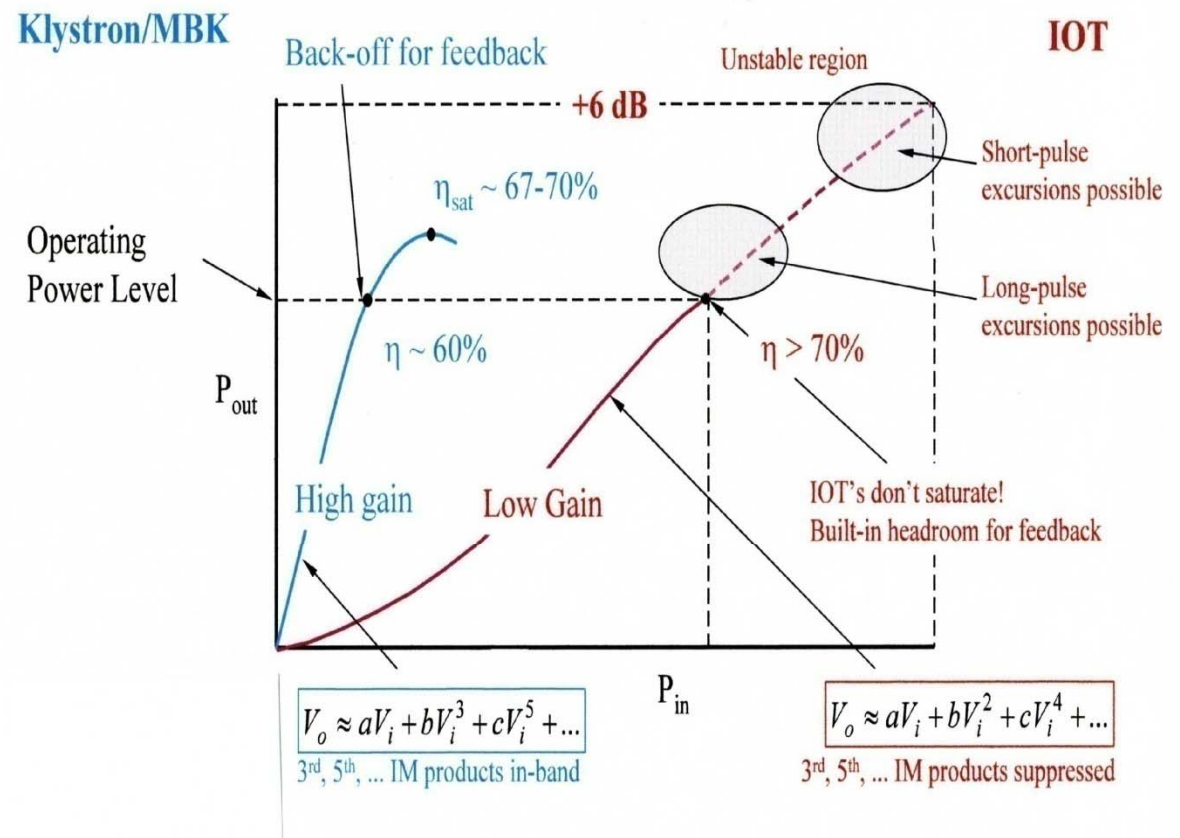
IOTs have operational advantages...

- Efficiency
- Absence of saturation
- Pulse-able via RF
- Small size
- High linearity

...and they are less expensive

Disadvantage:

- Low gain ( $\pm 22$  dB)





## Vacuum Electron Device Limitations for High-Power RF Sources

Thus IOTs have replaced klystrons in a growing number of applications.

Example:  
External cavity IOTs

Here: CHK2800W

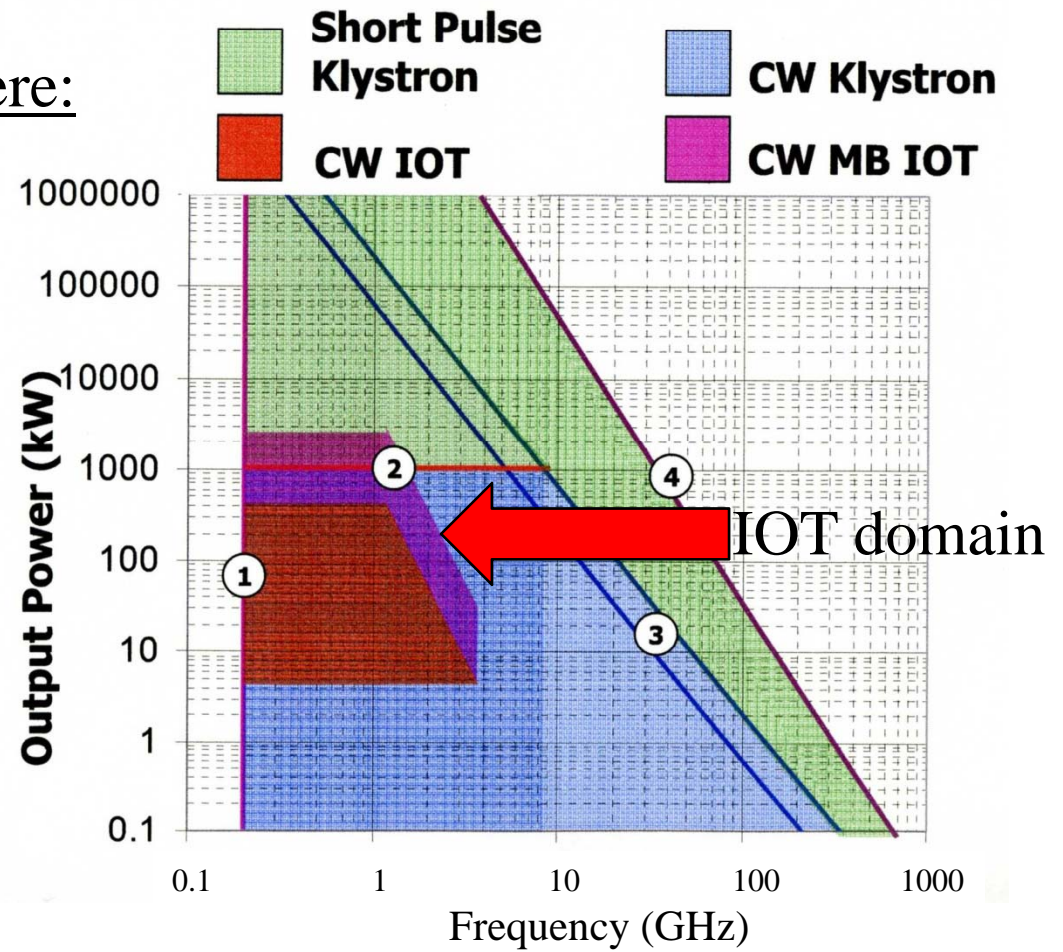
- tunable 470 – 860 MHz
- 130 kW in digital TV
- 80 kW CW at 500 MHz



# Vacuum Electron Device Limitations for High-Power RF Sources

IOT limitations discussed here:

- Size
- Average output power
- Operational frequency



## Vacuum Electron Device Limitations for High-Power RF Sources



Linear-beam IOTs feature a **size limitation** at frequencies lower than  $\sim 200$  MHz, due to their waveguide-type output cavities.

Example here:

“Chalk River” IOT  
250 kW CW at 267 MHz  
73 % efficiency

**Coaxial IOTs do not suffer from that restriction!**



## Vacuum Electron Device Limitations for High-Power RF Sources

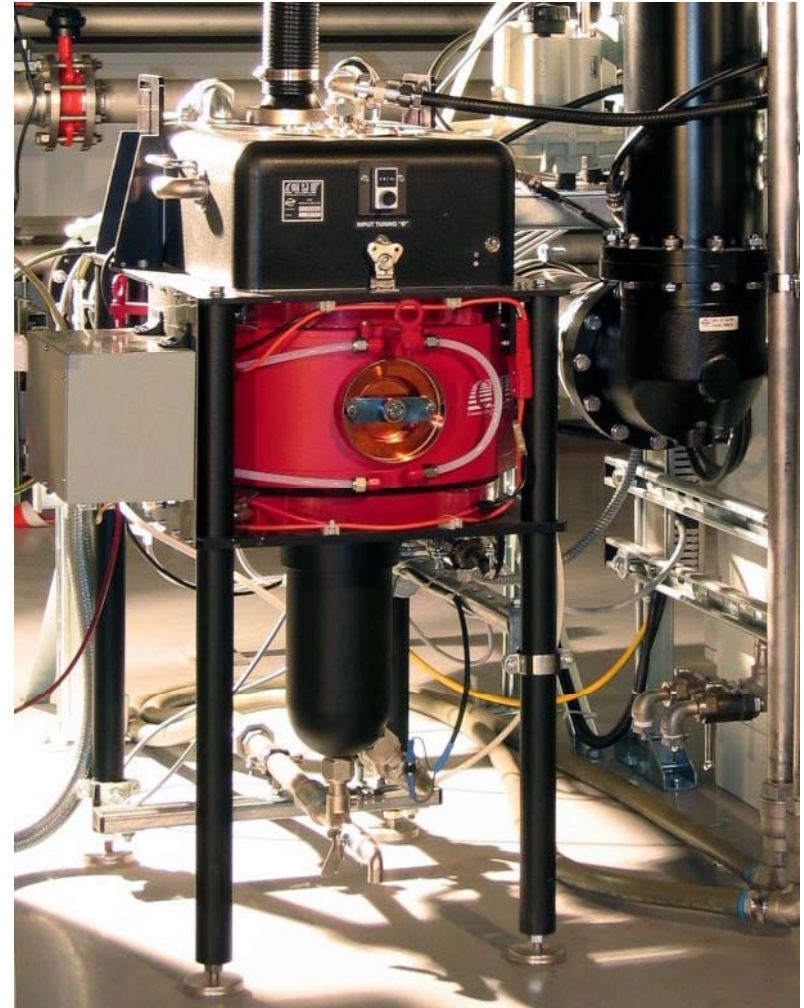
Safe operation of **external cavities**  
is **limited** to  $\sim 80$  kW.

Beyond that level integrated  
cavities become necessary.

This example:

500 MHz / 90 KW CW  
IOT K5H90W

(here at BESSY/PTB, Berlin)



## Vacuum Electron Device Limitations for High-Power RF Sources

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Higher power from a linear-beam IOT requires both higher **beam voltage** and higher **beam current**. Both are **limited**:

## Vacuum Electron Device Limitations for High-Power RF Sources

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- The beam voltage in continuous operation should not exceed 120 kV by a larger margin, independent from the size of the electron gun.



## Vacuum Electron Device Limitations for High-Power RF Sources

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- The beam voltage in continuous operation should not exceed 120 kV by a larger margin, independent from the size of the electron gun.
- Due to the control grid, overall perveances exceeding  $0.4 \mu\text{A}/\text{V}^{3/2}$  are difficult to achieve in class C operation in a linear-beam IOT.

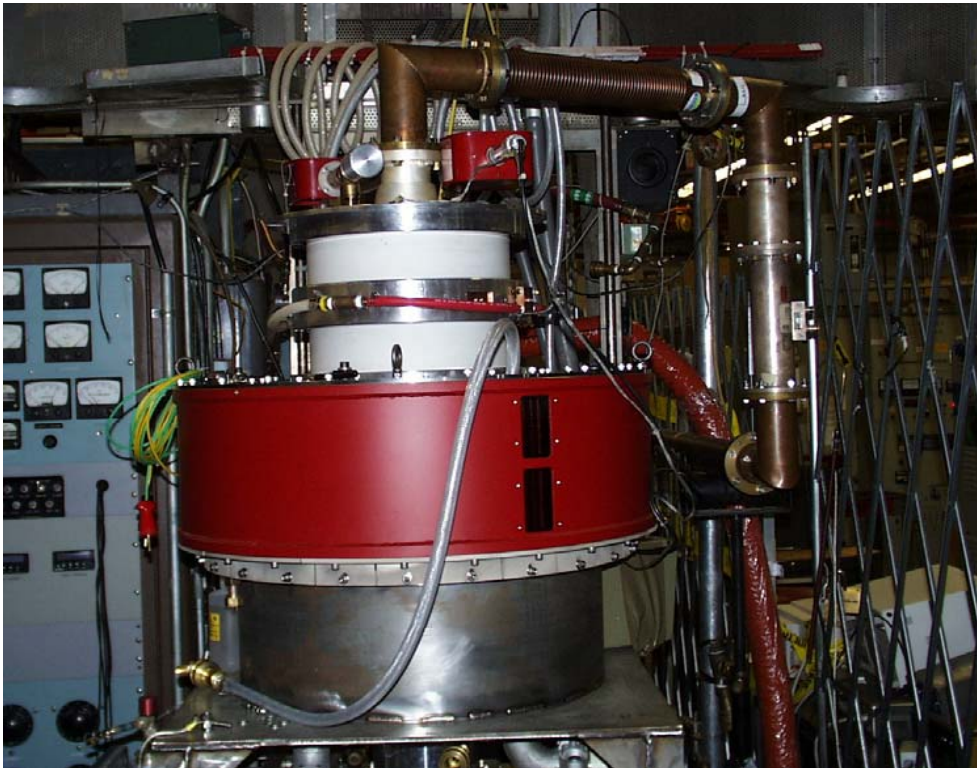
## Vacuum Electron Device Limitations for High-Power RF Sources

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- Due to the control grid, overall perveances exceeding  $0.4 \mu\text{A}/\text{V}^{3/2}$  are difficult to achieve in class C operation in a linear-beam IOT.
- IOT devices in the MW range therefore require different approaches.

## Vacuum Electron Device Limitations for High-Power RF Sources

Higher power from a linear-beam IOT requires both higher **beam voltage** and higher **beam current**. Both are **limited**.



First approach to 1 MW:

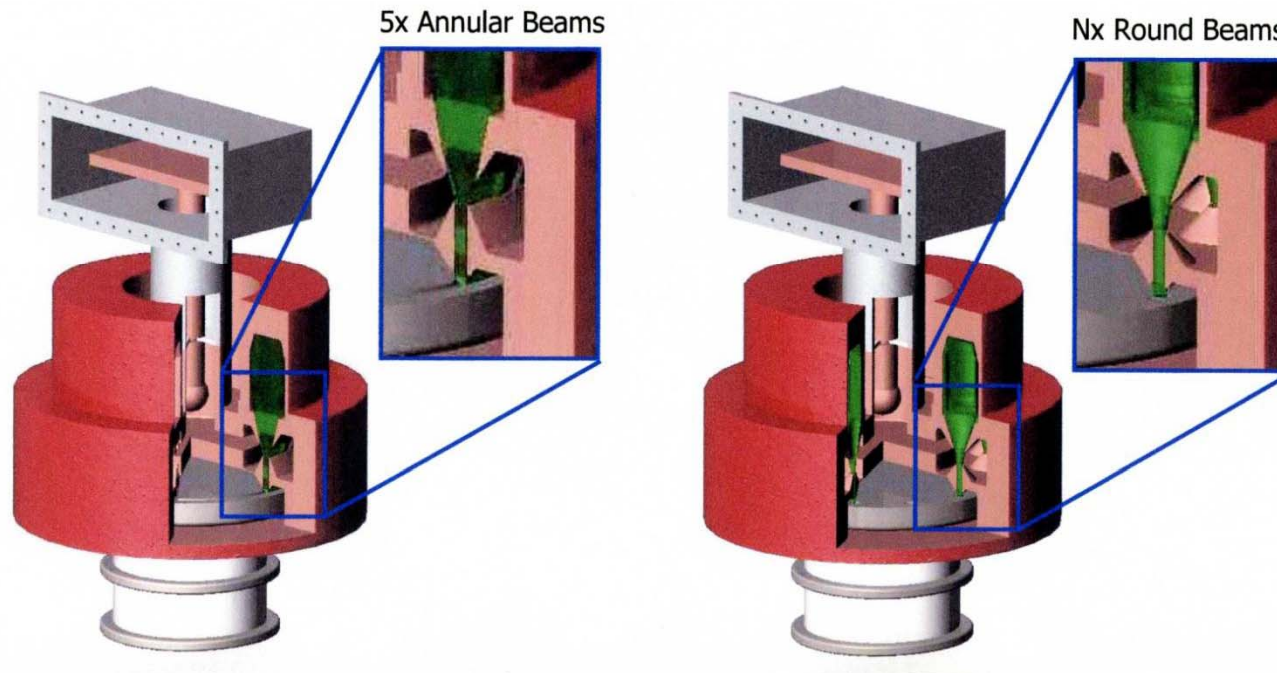
HOM-IOT with annular cathode and grid.

Development sponsored by LANL.

Proved the principle, but turned out to be too vulnerable.

# Vacuum Electron Device Limitations for High-Power RF Sources

Second approach to 1 MW level:  
HOM-IOT with  $n$  single beams.





# Vacuum Electron Device Limitations for High-Power RF Sources

## Presently under development:

- VHP-8330B – Round beam prototype

### *Typical Operating Parameters*

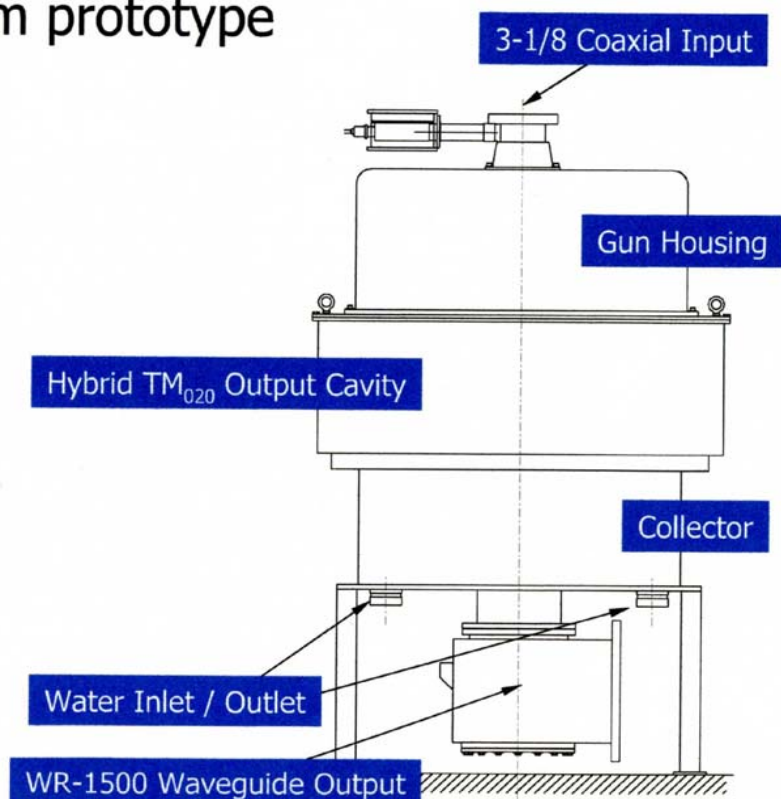
Power Output	1000	kW (min)
Beam Voltage	42	kV (nom)
Beam Current	33	A (nom)
Frequency	650-750	MHz
1dB Bandwidth	6	MHz (min)
Gain	25	dB (min)
Efficiency	71.5	% (min)
Cathode Loading	0.37	A/cm <sup>2</sup>

### *Electromagnet*

Main Coil Current	18	A
Main Coil Voltage	49	V

### *Size*

Diameter	30/76	in / cm
Height	51/130	in / cm
Weight	1000 / 450	lbs / kg



## Vacuum Electron Device Limitations for High-Power RF Sources

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The operational frequency of IOTs is limited due to **transit time limitations** in the cathode-grid space.



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For reliability reasons the distance between cathode and grid must be kept at a certain minimum.

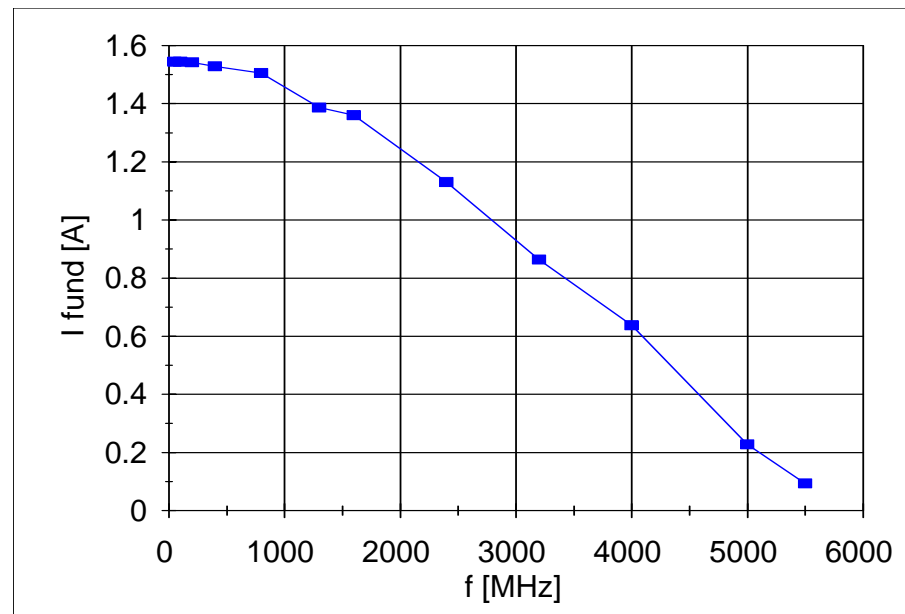
The resulting transit time restricts the achievable fundamental frequency RF current.

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Simulated example:



## Vacuum Electron Device Limitations for High-Power RF Sources

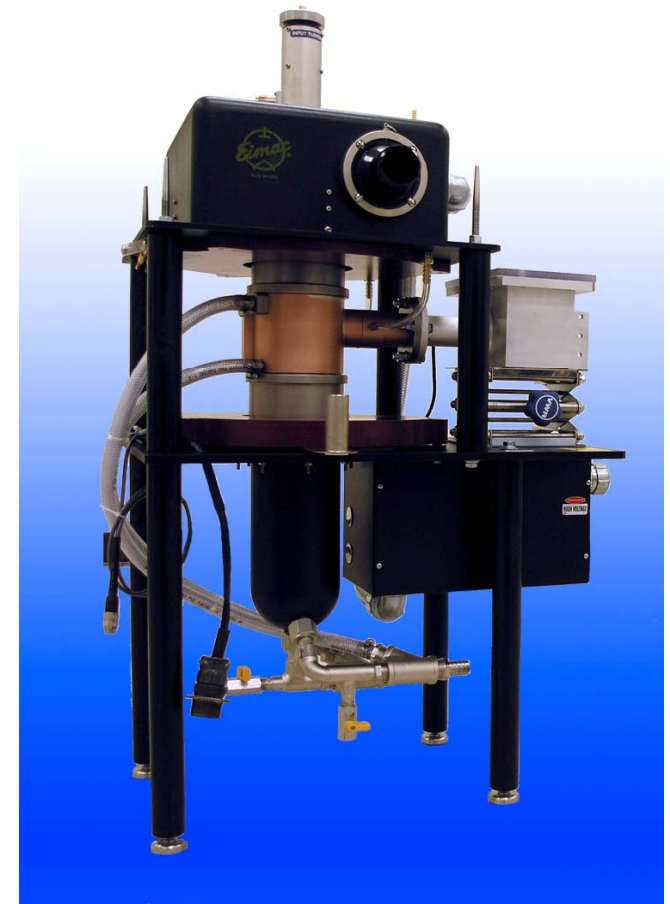
Frequencies up to 2 GHz still easily viable with existing technology

Example:

1.3 GHz IOT

30 kW CW

22 dB gain



## Vacuum Electron Device Limitations for High-Power RF Sources



Under development:

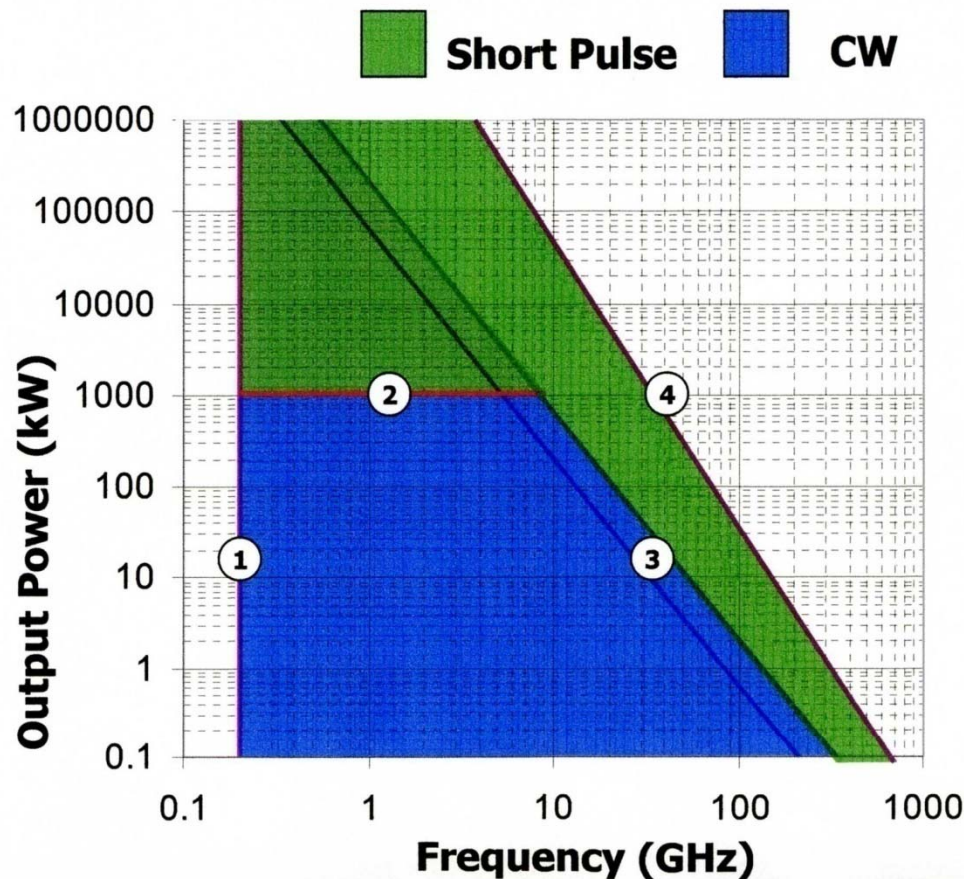
1.3 GHz High-Power IOT

60 – 120 kW CW

(Development sponsored by DESY)

## Vacuum Electron Device Limitations for High-Power RF Sources

Back to device limitations in the klystron sector:



Size (1) is much more an issue here than in the IOT domain.



## Vacuum Electron Device Limitations for High-Power RF Sources



For save degassing VEDs need to be pumped at high temperatures in exhaust ovens. Their size limits the size of the klystrons.

A klystron at the very size limit:

YK 1320, up to 3 MW long-pulse

Overall height: 5 m

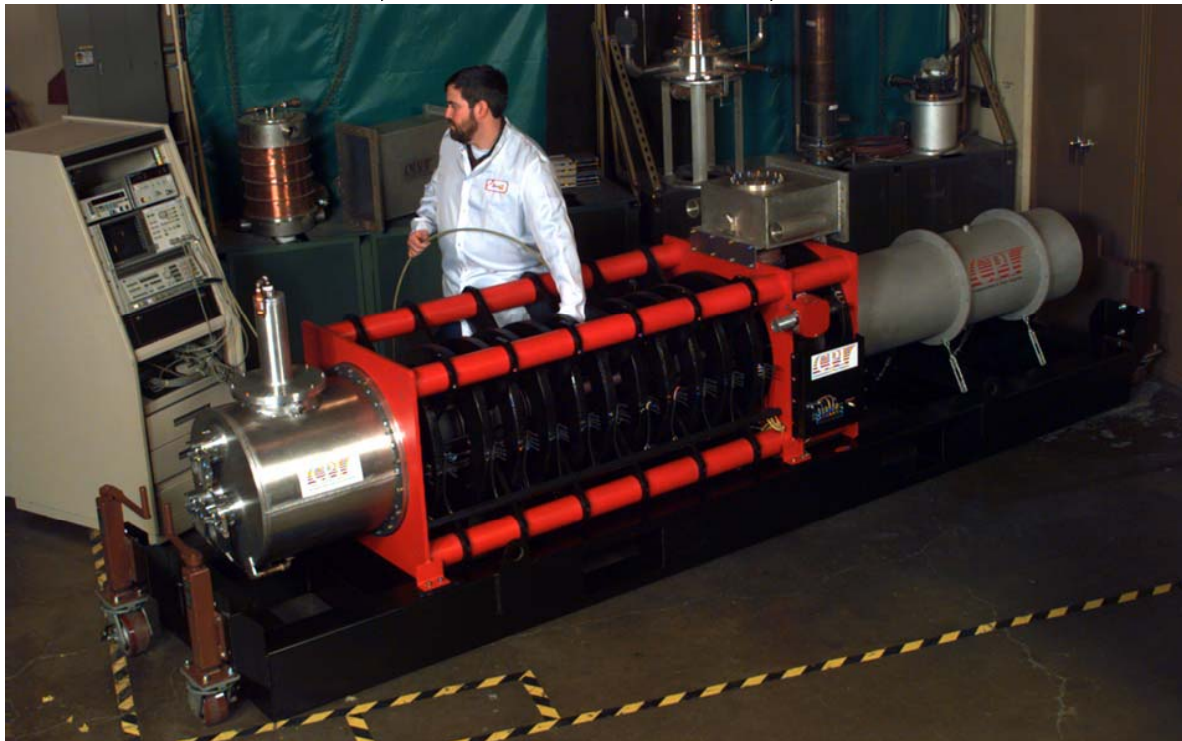
(The engineer in the foreground is 1.84 m tall)



## Vacuum Electron Device Limitations for High-Power RF Sources

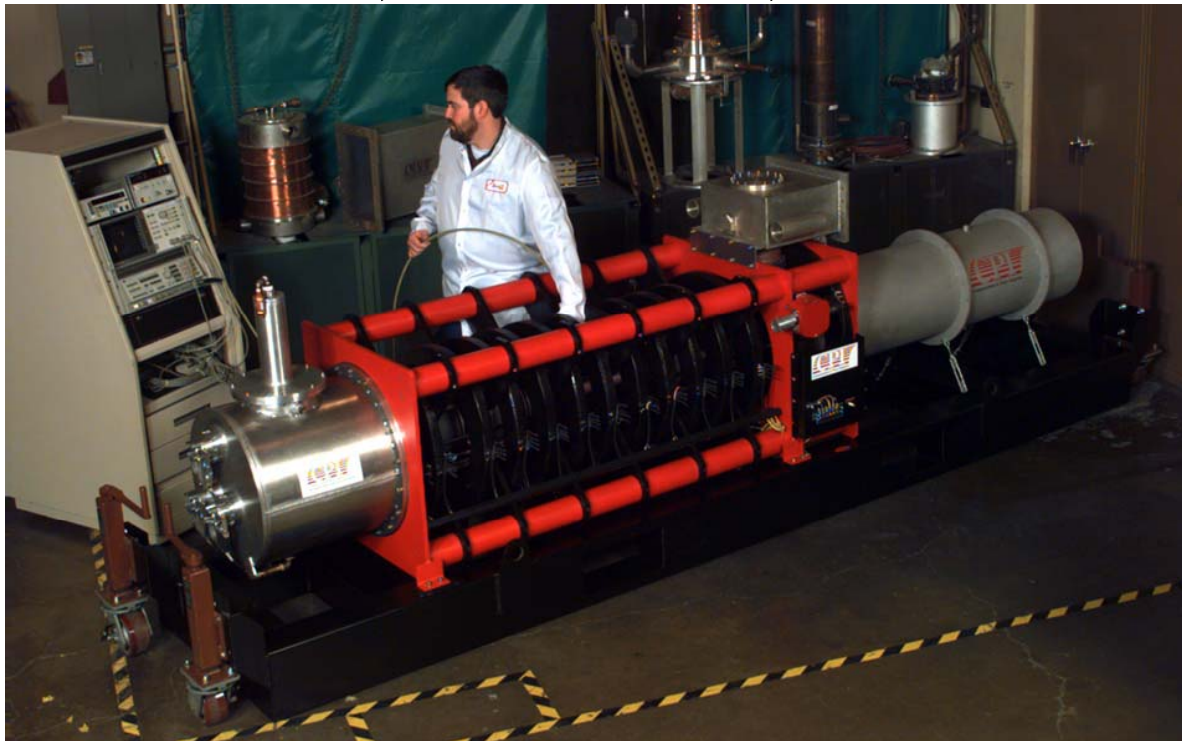
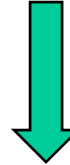
Still large, but easier to manufacture:

VKP-7952A/B, 700/704 MHz, 1 MW CW

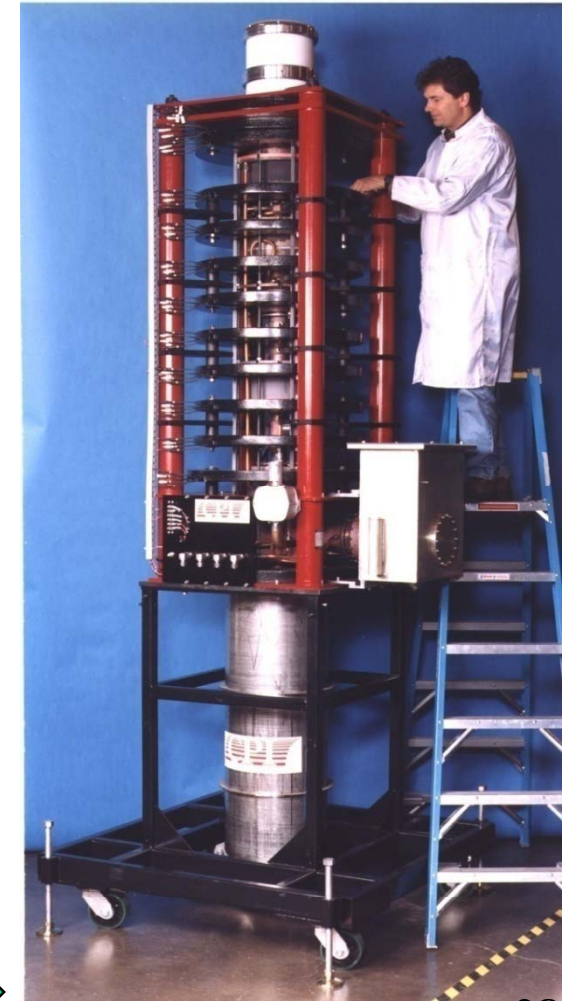
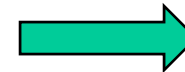


## Vacuum Electron Device Limitations for High-Power RF Sources

Still large, but easier to manufacture:  
VKP-7952A/B, 700/704 MHz, 1 MW CW



and VKP-7958A, 500 MHz, 800 kW CW



## Vacuum Electron Device Limitations for High-Power RF Sources



Like in the IOT domain, **high-voltage limitations** in the gun and **cathode emission density** considerations lead to multi-beam devices.



# Vacuum Electron Device Limitations for High-Power RF Sources

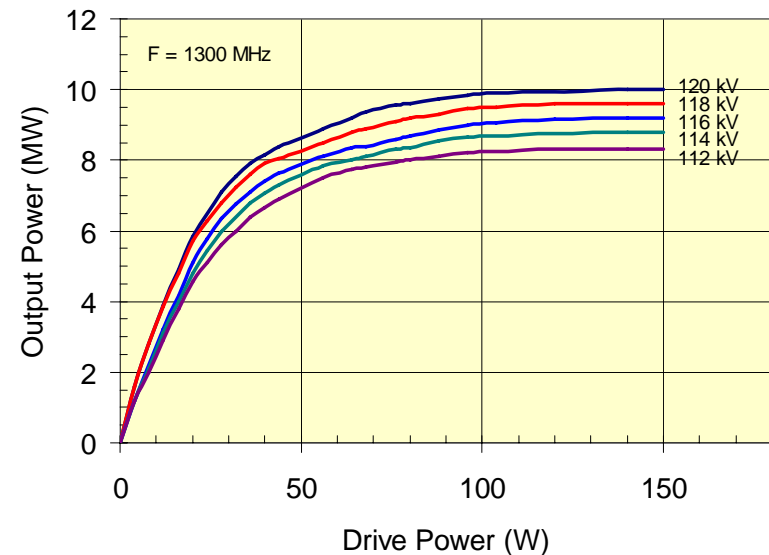


Like in the IOT domain, **high-voltage limitations** in the gun and **cathode emission density** considerations lead to multi-beam devices.

Example:

10 MW LP  
150 kW average  
1.3 GHz

(Development  
sponsored by  
DESY)



## Vacuum Electron Device Limitations for High-Power RF Sources

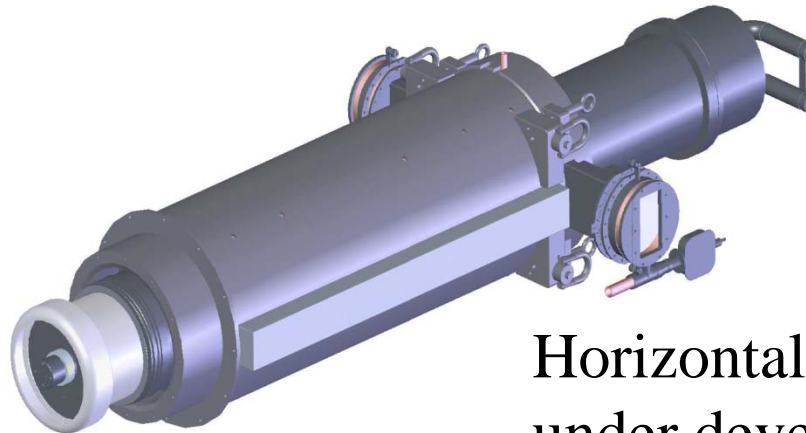


Not that **size** wouldn't be an issue here.  
But the **output windows** are close to their  
capability limits. Using two of them makes  
the task easier.

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Horizontal version  
under development





## Vacuum Electron Device Limitations for High-Power RF Sources



### Manufacturing Capacity and Reproducibility

Example:

VKP-8291A/B series

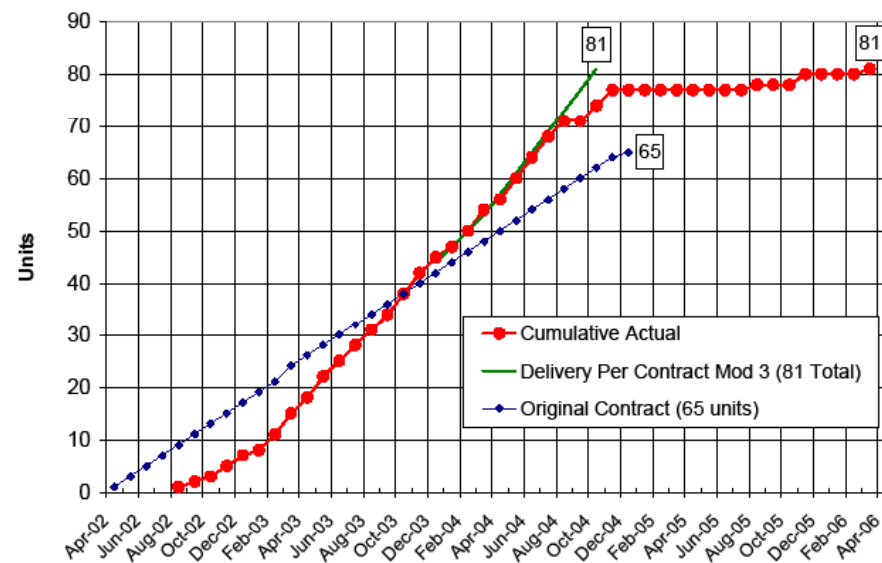
805 MHz, 550/700 kW,  
9 % duty cycle

used in the Spallation Neutron  
Source (SNS) at Oak Ridge  
National Laboratory (ORNL)

# Vacuum Electron Device Limitations for High-Power RF Sources



## Delivery Schedule of VKP-8291A

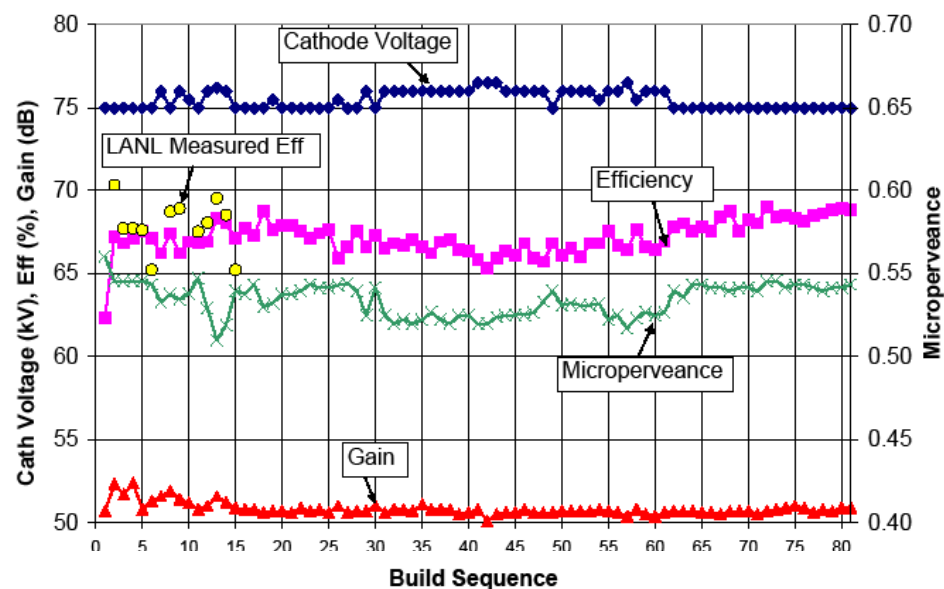


Delivery rate up to 3.3 units/month

# Vacuum Electron Device Limitations for High-Power RF Sources



## Production Reproducibility of VKP-8291A

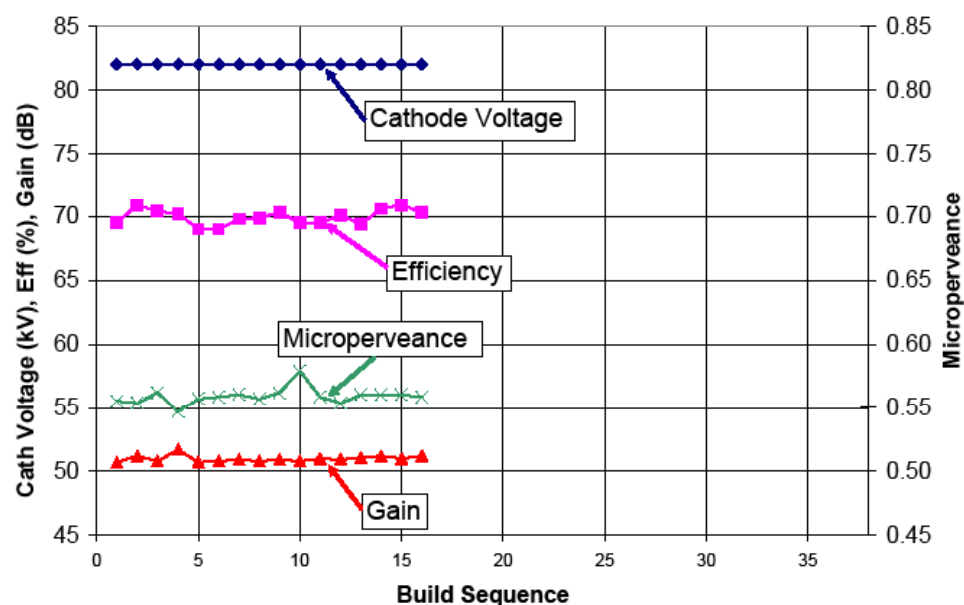


# Vacuum Electron Device Limitations for High-Power RF Sources



## Production Reproducibility of VKP-8291B

(Delivery rate 4 units/month)



## Vacuum Electron Device Limitations for High-Power RF Sources

Another powerful limitation is just **missing demand**.



## Vacuum Electron Device Limitations for High-Power RF Sources

Another powerful limitation is just **missing demand**.

Since money is in scarce supply practically everywhere,  
there is DEVELOPMENT in the case of demand, but only very  
little ongoing RESEARCH:

R & D

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R & D

Typical case: At 352 MHz, the CW output power level of  
klystrons has been stagnating at 1.3 MW for more than two  
decades by now.

But this is not a limitation. It could be 2 MW, or 3?

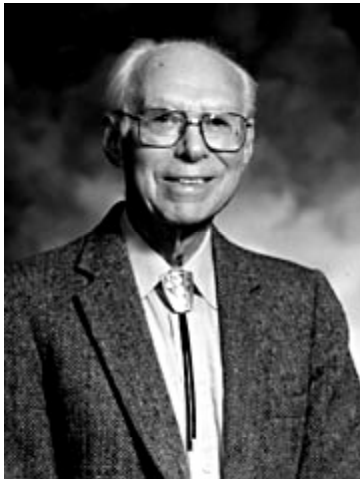
## Vacuum Electron Device Limitations for High-Power RF Sources

Finally, let's not forget one more important limitation:  
It's **blinkers** on the engineers' mind. We simply do not know  
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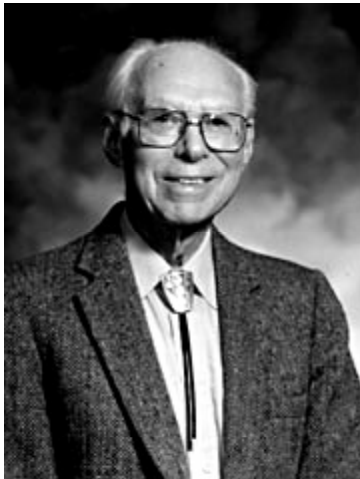
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**I thought about it the first time I saw it!**



# Vacuum Electron Device Limitations for High-Power RF Sources